Preface

This issue of *ECS Transactions* contains papers presented at the 13th Symposium on Thin Film Transistor Technologies (TFT 13) held in Honolulu, Hawaii, October 3-5, 2016. This symposium was sponsored by the Electronics and Photonics Division (EPD) of the Electrochemical Society. This is the 26th year of the symposium, which makes it the longest continuous held TFT conference in the world.

The editor wishes to express his sincere appreciation to the following people for their involvement in organizing and conducting the symposium: the authors and presenters of papers, symposium co-organizers, section chairs, my graduate assistants, and ECS staff.

There are 63 papers presented in the TFT 13 symposium. They are divided into 9 sessions: 1) Poly- and μc-Si TFTs, 2) Organic and Other Materials Based TFTs I, 3) Organic and Other Materials Based TFTs II, 4) Ge Materials Based TFTs, 5) Oxide TFT Processes, 6) Oxide TFT Devices, 7) Beyond Display Applications I, 8) Beyond Display Applications II, 9) Posters. Presenters are from universities, industry, and research institutes located in 9 countries or regions, *i.e.*, China, France, Hong Kong, Japan, Korea, Sweden, Taiwan, UK, and USA.

Papers in this issue of *ECS Transactions* are divided into 5 chapters. All papers are published as received, without alteration of their technical contents.

This symposium clearly shows the progress of the TFT science and technology:
— There are still strong R&D activities on the Si-based TFT technology from academia and industry. The main focus is on the development of the manufacturable, high-mobility, crystalline TFTs on the glass or flexible substrate.
— Organic and Ge-related materials for TFTs have been continuously explored.
— Currently, oxide TFTs have attracted most studies. The hottest topics are: new materials for better device performance or reliability, low temperature processes, influences of processes or structures on device characteristics, etc.,
— There are a large number of activities on TFT applications beyond displays. This trend was first forecasted at the beginning of the TFT symposium in 1992. Since TFTs are substrate-independent, low-cost devices, the range of applications is unmatched by other solid state devices.

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